

SANYO	No.3234	2SC4480
NPN Epitaxial Planar Silicon Transistor		
Low-Frequency General-Purpose Amp, General Driver Applications		

Features

- Large current capacity
- Adoption of MBIT process
- High DC current gain
- Low collector-to-emitter saturation voltage
- High V_{EBO}

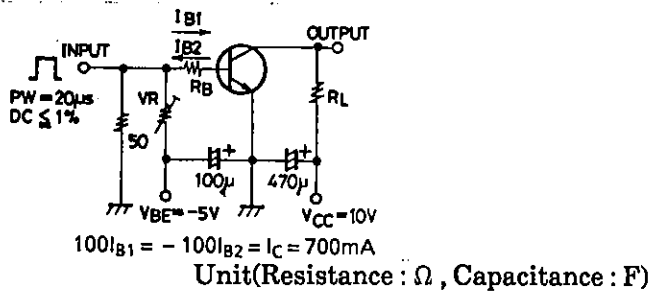
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Collector to Base Voltage	V_{CBO}	30	V	
Collector to Emitter Voltage	V_{CEO}	25	V	
Emitter to Base Voltage	V_{EBO}	15	V	
Collector Current	I_C	2	A	
Collector Current(Pulse)	I_{CP}	4	A	
Base Current	I_B	0.4	A	
Collector Dissipation	P_C	1	W	
Junction Temperature	T_j	150	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

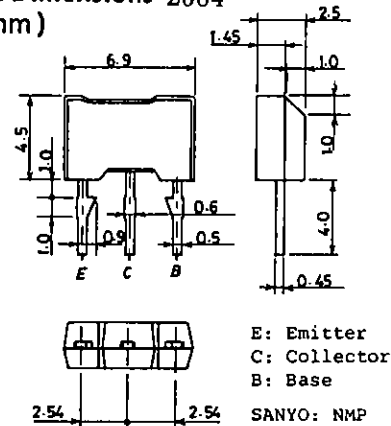
Electrical Characteristics at $T_a = 25^\circ\text{C}$

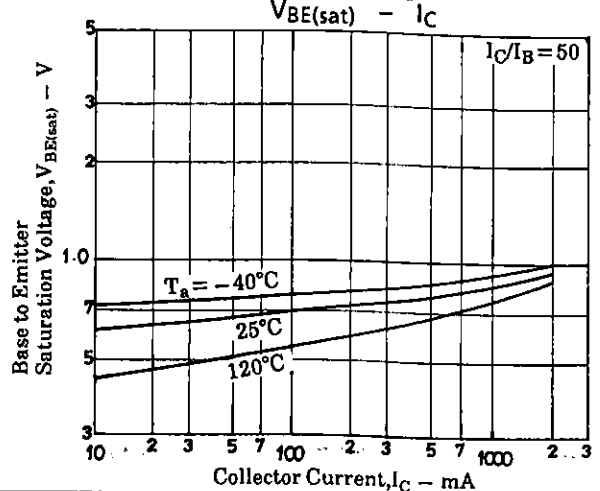
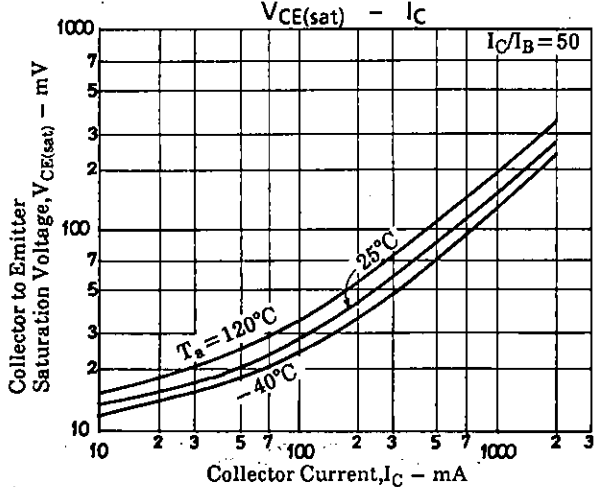
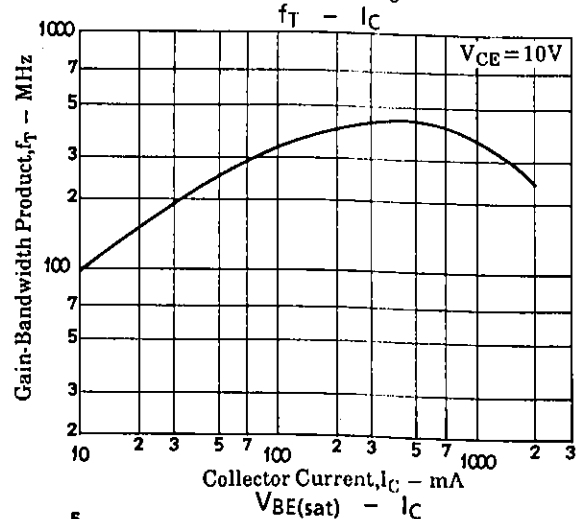
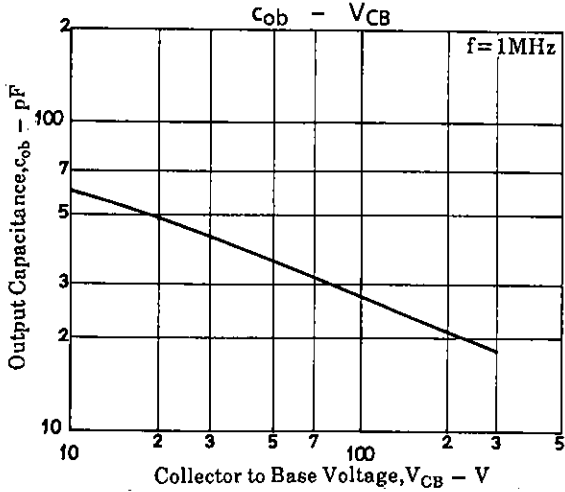
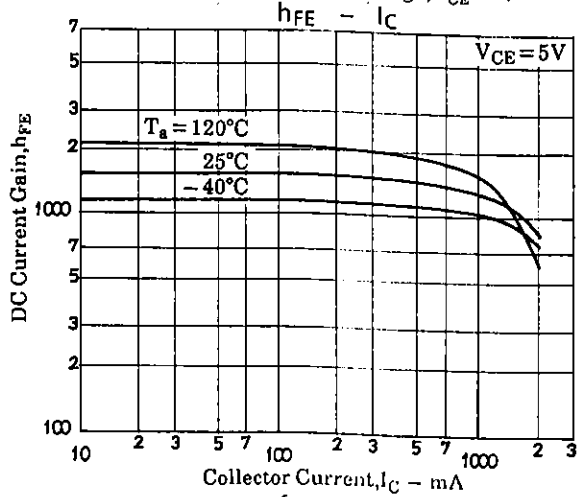
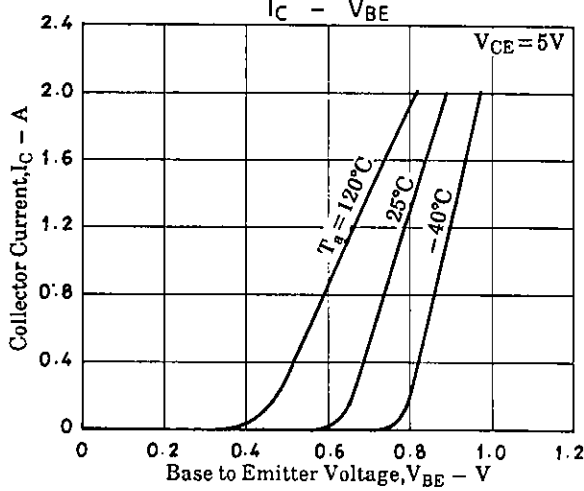
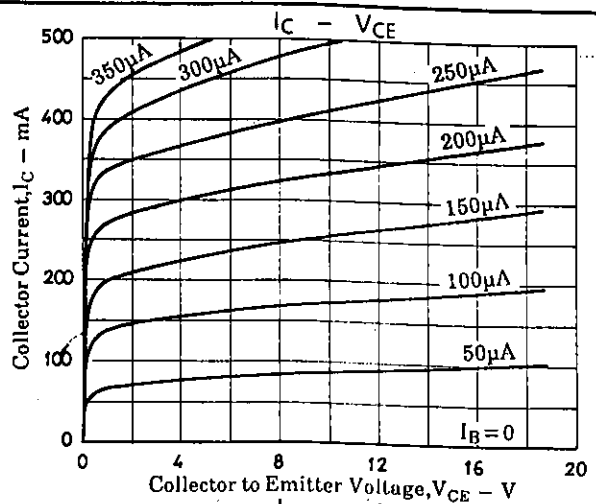
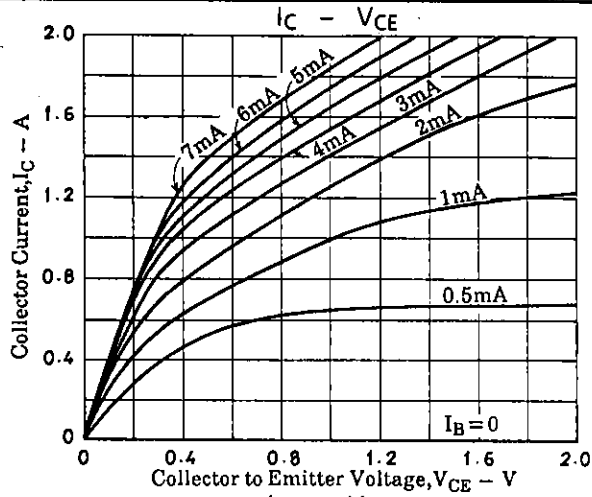
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = 20\text{V}, I_E = 0$			100	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 10\text{V}, I_C = 0$			100	nA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = 5\text{V}, I_C = 500\text{mA}$	800	1500	3200	
	$h_{FE}(2)$	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	600			
Gain-Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 50\text{mA}$		260		MHz
Output Capacitance	c_{ob}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		27		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 1\text{A}, I_B = 20\text{mA}$	0.15		0.5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 1\text{A}, I_B = 20\text{mA}$	0.85		1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	30			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, R_{BE} = \infty$	25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	15			V
Turn-ON Time	t_{on}	See specified Test Circuit.		0.14		μs
Storage Time	t_{stg}	"		1.35		μs
Fall Time	t_f	"		0.1		μs

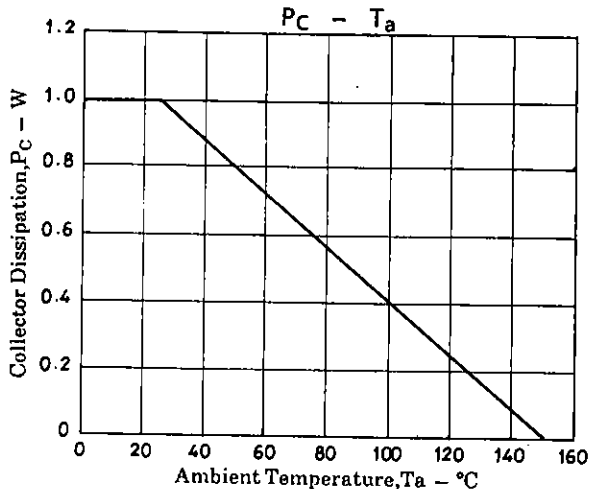
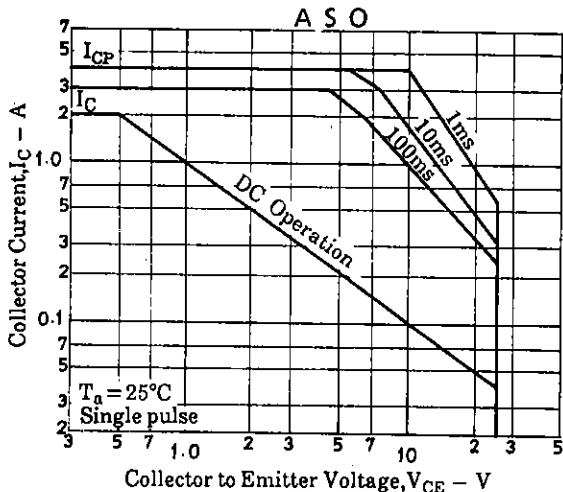
Switching Time Test Circuit



Package Dimensions 2064
(unit: mm)







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